



Bulk GaN Substrates



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Overview

Kyma has over 20 years experience of research, development, partnership, and innovation for bulk GaN substrates. Using world class Halide Vapor Phase Epitaxy (HVPE), lapping, and polishing processes; Kyma is offering bulk GaN substrates with outstanding crystalline quality, electrical properties, and usable surface area.

Available in 10 mm x 10 mm, 2-inch and 4-inch diameters along with excellent prices, Kyma is offering bulk GaN that is truly a commercially-viable innovation.



General Specs

	N-type	Semi-Insulating
Available diameters	10 mm x 10 mm, 2 inch, 4 inch	10 mm x 10 mm, 2 inch, 4 inch
Resistivity	≤0.02 Ω cm	> 1E8 Ω cm
Dislocation Density	< 1E6 cm ⁻²	
XRD Linewidths	002 Reflection: < 100 arcsec 102 Reflection: < 100 arcsec	
Polarities	Ga-face: standard N-Face: optional	

Thickness

	10 mm sq	2 inch	4 inch
Diameter	10 mm x 10 mm ± 0.3 mm	50.8 ± 0.3 mm	100 mm ± 0.3 mm
Thickness	400 μm ± 30 μm	400 μm ± 30 μm	450 μm ± 30 μm
TTV	Not Measured	≤ 20 µm	≤40 μm
Warp	Not Measured	≤ 30 µm	≤80 µm



Pitting -

Every wafer is inspected for pitting and measured for pit density (#/cm²). They are then classified into two categories

Pit Density #/cm ²	
Production Grade	≤ 0.5
Research Grade	≤ 1.5

	10 mm x 10 mm	2″	4"
Production Grade	≤ 1	≤ 10	≤ 40
Research Grade	≤ 2	≤ 30	≤ 120

Surface -

Polarity	Front Side	Back Side	
Ga-Face		RMS < 5.0 nm	
N-Face	RMS < 1.0 nm		

Orientation -



	10 mm x 10 mm	2″	4″
Major Flat Length	N/A	16 mm	32 mm
Minor Flat Length	N/A	8 mm	8 mm

* All measurements are ± 1 mm

Orientation	(0001) Ga-Face, c-plane (standard); (000-1) N-face (optional)
Offcut Toward m-plane	0.6° ± 0.12° toward [10-10]
Offcut Toward Orthogonal a-plane	0.0°±0.2° toward [1-210]
Major Orientation Flat Plane	(10-10) m-plane

For sales and business-related inquiries please contact sales@kymatech.com

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